

Z R Kudrynskyi

List of Publications by Citations

Source: <https://exaly.com/author-pdf/9088431/z-r-kudrynskyi-publications-by-citations.pdf>

Version: 2024-04-28

This document has been generated based on the publications and citations recorded by exaly.com. For the latest version of this publication list, visit the link given above.

The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

68

papers

2,381

citations

18

h-index

48

g-index

73

ext. papers

2,880

ext. citations

6

avg, IF

4.61

L-index

#	Paper	IF	Citations
68	High electron mobility, quantum Hall effect and anomalous optical response in atomically thin InSe. <i>Nature Nanotechnology</i> , 2017 , 12, 223-227	28.7	723
67	Tuning the bandgap of exfoliated InSe nanosheets by quantum confinement. <i>Advanced Materials</i> , 2013 , 25, 5714-8	24	419
66	High broad-band photoresponsivity of mechanically formed InSe-graphene van der Waals heterostructures. <i>Advanced Materials</i> , 2015 , 27, 3760-6	24	252
65	The direct-to-indirect band gap crossover in two-dimensional van der Waals Indium Selenide crystals. <i>Scientific Reports</i> , 2016 , 6, 39619	4.9	114
64	Quantum confinement and photoresponsivity of In_2Se_3 nanosheets grown by physical vapour transport. <i>2D Materials</i> , 2016 , 3, 025030	5.9	68
63	Design of van der Waals interfaces for broad-spectrum optoelectronics. <i>Nature Materials</i> , 2020 , 19, 299-304	30.4	64
62	Engineering p-n junctions and bandgap tuning of InSe nanolayers by controlled oxidation. <i>2D Materials</i> , 2017 , 4, 025043	5.9	63
61	Room Temperature Electroluminescence from Mechanically Formed van der Waals III-VI Homojunctions and Heterojunctions. <i>Advanced Optical Materials</i> , 2014 , 2, 1064-1069	8.1	61
60	Epitaxial growth of InSe and SnSe and In_2Se_3 on GaSe . <i>2D Materials</i> , 2018 , 5, 035026	5.9	55
59	Quantum confined acceptors and donors in InSe nanosheets. <i>Applied Physics Letters</i> , 2014 , 105, 221909	3.4	53
58	Interlayer Band-to-Band Tunneling and Negative Differential Resistance in van der Waals BP/InSe Field-Effect Transistors. <i>Advanced Functional Materials</i> , 2020 , 30, 1910713	15.6	41
57	Giant Quantum Hall Plateau in Graphene Coupled to an InSe van der Waals Crystal. <i>Physical Review Letters</i> , 2017 , 119, 157701	7.4	33
56	Gate-Defined Quantum Confinement in InSe-Based van der Waals Heterostructures. <i>Nano Letters</i> , 2018 , 18, 3950-3955	11.5	33
55	Two-Dimensional Covalent Crystals by Chemical Conversion of Thin van der Waals Materials. <i>Nano Letters</i> , 2019 , 19, 6475-6481	11.5	26
54	Biexciton formation and exciton coherent coupling in layered GaSe. <i>Journal of Chemical Physics</i> , 2015 , 142, 212422	3.9	24
53	Formation and Healing of Defects in Atomically Thin GaSe and InSe. <i>ACS Nano</i> , 2019 , 13, 5112-5123	16.7	23
52	Mechanism of excitonic dephasing in layered InSe crystals. <i>Physical Review B</i> , 2014 , 89,	3.3	22

51	Coherent acoustic phonons in van der Waals nanolayers and heterostructures. <i>Physical Review B</i> , 2018 , 98,	3.3	19
50	High-Frequency Elastic Coupling at the Interface of van der Waals Nanolayers Imaged by Picosecond Ultrasonics. <i>ACS Nano</i> , 2019 , 13, 11530-11537	16.7	15
49	Magnetic properties and surface morphology of layered In ₂ Se ₃ crystals intercalated with cobalt. <i>Physics of the Solid State</i> , 2013 , 55, 1148-1155	0.8	14
48	Resonant tunnelling into the two-dimensional subbands of InSe layers. <i>Communications Physics</i> , 2020 , 3,	5.4	13
47	Nanomechanical probing of the layer/substrate interface of an exfoliated InSe sheet on sapphire. <i>Scientific Reports</i> , 2016 , 6, 26970	4.9	13
46	Photoquantum Hall Effect and Light-Induced Charge Transfer at the Interface of Graphene/InSe Heterostructures. <i>Advanced Functional Materials</i> , 2019 , 29, 1805491	15.6	13
45	Inter-Flake Quantum Transport of Electrons and Holes in Inkjet-Printed Graphene Devices. <i>Advanced Functional Materials</i> , 2021 , 31, 2007478	15.6	13
44	Improved performance of InSe field-effect transistors by channel encapsulation. <i>Semiconductor Science and Technology</i> , 2018 , 33, 06LT01	1.8	11
43	Enhanced Optical Emission from 2D InSe Bent onto Si-Pillars. <i>Advanced Optical Materials</i> , 2020 , 8, 2000888	8.8	10
42	Schottky-barrier thin-film transistors based on HfO ₂ -capped InSe. <i>Applied Physics Letters</i> , 2019 , 115, 033502	5.02	10
41	Large Tunneling Magnetoresistance in van der Waals Ferromagnet/Semiconductor Heterojunctions. <i>Advanced Materials</i> , 2021 , e2104658	24	10
40	Van der Waals SnSe ₂ (1-x)S _{2x} Alloys: Composition-Dependent Bowing Coefficient and Electron-Phonon Interaction. <i>Advanced Functional Materials</i> , 2020 , 30, 1908092	15.6	10
39	Graphene-InSe-graphene van der Waals heterostructures. <i>Journal of Physics: Conference Series</i> , 2015 , 647, 012001	0.3	9
38	Highly-mismatched InAs/InSe heterojunction diodes. <i>Applied Physics Letters</i> , 2016 , 109, 182115	3.4	9
37	The Interaction of Hydrogen with the van der Waals Crystal -InSe. <i>Molecules</i> , 2020 , 25,	4.8	8
36	Surface morphology and electrical properties of Au/Ni/C/n-Ga ₂ O ₃ /p-GaSe/KNO ₃ hybrid structures fabricated on the basis of a layered semiconductor with nanoscale ferroelectric inclusions. <i>Semiconductors</i> , 2012 , 46, 342-353	0.7	8
35	Defect-Assisted High Photoconductive UV-Visible Gain in Perovskite-Decorated Graphene Transistors. <i>ACS Applied Electronic Materials</i> , 2020 , 2, 147-154	4	8
34	Optical size effect in In ₂ O ₃ nanostructured films. <i>Semiconductors</i> , 2013 , 47, 345-348	0.7	7

33	Morphology of nanostructures formed on the van der Waals surface of GaSe layered crystals annealed in sulfur vapor. <i>Physics of the Solid State</i> , 2011 , 53, 2154-2159	0.8	7
32	Photoluminescence dynamics in few-layer InSe. <i>Physical Review Materials</i> , 2020 , 4,	3.2	7
31	Fabrication and characterization of photosensitive n-ZnO/p-InSe heterojunctions. <i>Thin Solid Films</i> , 2015 , 582, 253-257	2.2	6
30	Magnetotransport and lateral confinement in an InSe van der Waals Heterostructure. <i>2D Materials</i> , 2018 , 5, 035040	5.9	6
29	Structure of oxidized and unoxidized end faces of GaSe layered crystals. <i>Inorganic Materials</i> , 2014 , 50, 339-343	0.9	6
28	Effect of low-temperature annealing on the quality of InSe layered single crystals and the characteristics of n-InSe/p-InSe heterojunctions. <i>Semiconductors</i> , 2014 , 48, 545-550	0.7	6
27	Controlled synthesis and characterization of highly ordered core-shell nickel-carbon nanoparticle arrays on the van der Waals surfaces of layered semiconductor crystals. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2014 , 211, 342-350	1.6	6
26	Fabrication and Characterization of Photosensitive n-CdO/p-InSe Heterojunctions. <i>Acta Physica Polonica A</i> , 2013 , 124, 720-723	0.6	6
25	Photosensitive anisotype n-ZnSe/p-InSe and n-ZnSe/p-GaSe heterojunctions. <i>Technical Physics</i> , 2014 , 59, 1205-1208	0.5	5
24	Electrical and photoelectric properties of n-CdO-p-InSe anisotype heterojunctions. <i>Semiconductors</i> , 2013 , 47, 943-946	0.7	5
23	Room Temperature Uniaxial Magnetic Anisotropy Induced By Fe-Islands in the InSe Semiconductor Van Der Waals Crystal. <i>Advanced Science</i> , 2018 , 5, 1800257	13.6	5
22	Nanocomposite structures grown by inserting ionic salt RbNO ₃ into van der Waals gaps of III-VI compound layered semiconductors. <i>Solid State Ionics</i> , 2015 , 273, 59-65	3.3	4
21	Spectral anisotropy of a photoresponse from heterojunctions based on GaSe and InSe layered crystals. <i>Technical Physics</i> , 2014 , 59, 407-410	0.5	4
20	Composite Nanostructures Based on a Layered Semiconductor with Nanoscale 3D Ferroelectric Inclusions (p-GaSe Intercalated by KNO ₃). <i>Sensor Letters</i> , 2013 , 11, 1549-1554	0.9	4
19	Anomalous Low Thermal Conductivity of Atomically Thin InSe Probed by Scanning Thermal Microscopy. <i>Advanced Functional Materials</i> , 2021 , 31, 2008967	15.6	4
18	Ferroelectric semiconductor junctions based on graphene/In ₂ Se ₃ /graphene van der Waals heterostructures. <i>2D Materials</i> , 2021 , 8, 045020	5.9	4
17	On the photoplectrochromism coefficient and its temperature dynamics in native oxide-p-InSe heterojunctions. <i>Semiconductors</i> , 2014 , 48, 776-778	0.7	3
16	Fabrication and characterization of PbSe nanostructures on van der Waals surfaces of GaSe layered semiconductor crystals. <i>Nanotechnology</i> , 2015 , 26, 465601	3.4	3

15	Structure and magnetic properties of cobalt-intercalated layered InSe crystals. <i>Technical Physics</i> , 2014 , 59, 1462-1465	0.5	2
14	Sensitive elements of pressure transducers made of layered intercalated InSe, GaSe, and Bi ₂ Te ₃ crystals. <i>Technical Physics</i> , 2013 , 58, 1840-1843	0.5	2
13	Morphology, chemical composition, and electrical characteristics of hybrid (Ni-C) nanocomposite structures grown on the van der Waals GaSe(0001) surface. <i>Physics of the Solid State</i> , 2014 , 56, 2118-2130	0.8	2
12	Characterization of potential nanoporous sodium titanate film formation on Ti6Al4V and TiO ₂ microspherical substrates via wet-chemical alkaline conversion. <i>Materials Characterization</i> , 2022 , 185, 111760	3.9	2
11	Tunable spin-orbit coupling in two-dimensional InSe. <i>Physical Review B</i> , 2021 , 104,	3.3	2
10	Resonance and antiresonance in Raman scattering in GaSe and InSe crystals. <i>Scientific Reports</i> , 2021 , 11, 924	4.9	2
9	Photoelectric properties of n-ITO/p-GaTe heterojunctions. <i>Semiconductors</i> , 2015 , 49, 600-603	0.7	1
8	Electrochemical, optical, and magnetic properties of Ni _x GaSe (0 Inorganic Materials, 2015 , 51, 1086-1089)	0.9	0
7	High-Performance Phototransistors by Alumina Encapsulation of a 2D Semiconductor with Self-Aligned Contacts. <i>Advanced Electronic Materials</i> , 2100954	6.4	0
6	Preparation of Nanocomposite Magnetic Compounds Based on Layered Semiconductors by Means of Electrochemical Intercalation in a Gradient Magnetic Field. <i>Acta Physica Polonica A</i> , 2016 , 130, 773-777	0.6	0
5	Terahertz control of photoluminescence emission in few-layer InSe. <i>Applied Physics Letters</i> , 2022 , 120, 092104	3.4	0
4	Influence of Optical Illumination on the Electric Impedance of Composite Nanostructures Based on p-GaSe Layered Semiconductor with 3D Nanodimensional Inclusions of KNO ₃ Ferroelectric. <i>Russian Physics Journal</i> , 2014 , 57, 642-656	0.7	
3	Morphology of Van der Waals surfaces and magnetic hysteresis in cobalt intercalated InTe. <i>Functional Materials</i> , 2015 , 22, 327-331	0.6	
2	Physical properties of layered FeIn ₂ Se ₄ single crystals. <i>Functional Materials</i> , 2016 , 23, 557-560	0.6	
1	Charge Carrier Transport in Van Der Waals Semiconductor InSe Intercalated with RbNO ₃ Probed by Direct Current Methods. <i>Applied Sciences (Switzerland)</i> , 2021 , 11, 5181	2.6	